

Switchmode Dual Ultrafast Power Rectifiers

Designed for use in switching power supplies inverters and as freewheeling diodes. These state-of-the-art devices have the following

Features

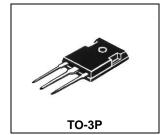
- *High Surge Capacity
- *Low Power Loss, High efficiency
- *150 °C Operating Junction Temperature
- *Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- * High-Switching Speed 50 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- *Pb free
- *In compliance with EU RoHs directives





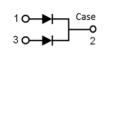
ULTRA FAST RECTIFIERS

16 AMPERES 400 VOLTS



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DIM	MILLIMETERS			
וווטו	MIN	MAX		
Α	20.80	21.80		
В	15.38	16.20		
С	1.90	2.70		
D	5.10	6.10		
E	14.50	15.50		
F	11.20	13.20		
G	3.75	4.35		
Н	1.90	2.30		
- 1	2.90	3.30		
J	1.00	1.40		
K	5.26	5.66		
L	19.50	20.50		
M	4.68	5.36		
N	2.30	2.60		
0	3.45	3.85		
Р	0.48	0.72		



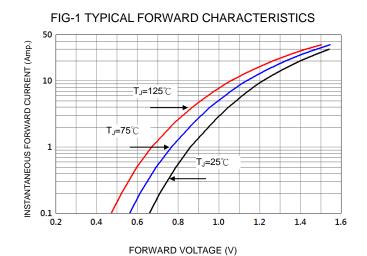
MAXIMUM RATINGS

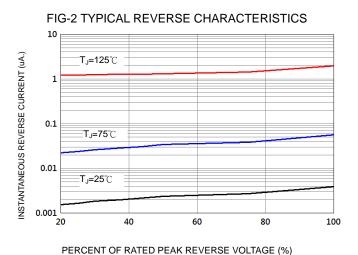
Characteristic	Symbol	UE16D40C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	400	V
RMS Reverse Voltage	V _{R(RMS)}	280	V
Average Rectifier Forward Current (per diode) Total Device (Rated V _R)	I _{F(AV)}	8 16	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	16	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-ware, single phase, 60Hz)	I _{FSM}	125	А
Operating and Storage Junction Temperature Range	T_J , T_{stg}	-65 to +150	$^{\circ}\!\mathbb{C}$

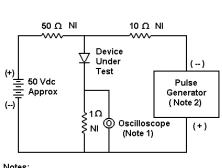
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Тур.	Max.	Unit		
Maximum Instantaneous Forward Voltage ($I_F = 8.0 \text{ Amp } T_C = 25^{\circ}C$) ($I_F = 8.0 \text{ Amp } T_C = 125^{\circ}C$)	V _F		1.15 1.00	1.40	>		
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _C = 25°C) (Rated DC Voltage, T _C = 125°C)	I _R		0.01 5	10 	uA		
Reverse Recovery Time (I _F = 0.5 A, I _R =1.0 , I _{rr} =0.25 A)	Trr		24	35	ns		

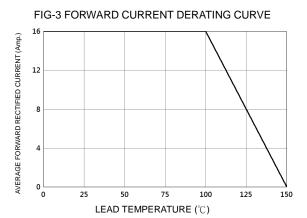


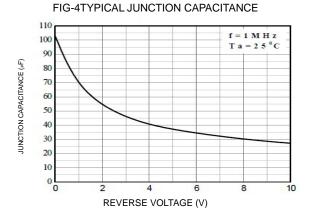


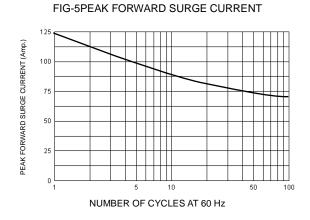


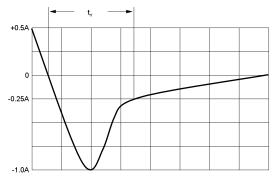


Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50Ω









Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram